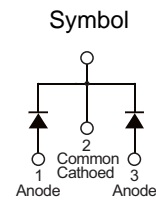


### ■ PRODUCT CHARACTERISTICS

|                |        |
|----------------|--------|
| VR(@IC=0.5mA)  | 100V   |
| VF(Typ@IF=15A) | 0.83V  |
| IR(@VR=100V)   | 0.05mA |
| ID             | 30A    |

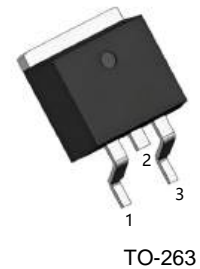


### ■ MECHANICAL CHARACTERISTICS

- \* Case: epoxy,molded
- \* Finish:all external surfaces corrosion resistant and terminal
- \* Leads are readily solderable
- \* Leads temperature for soldering purposes:  
260°C Max for 10 seconds

### ■ FEATURES

- \* Low forward voltage
- \* Low power loss/high efficiency
- \* Low stored charge majority carrier conduction
- \* Pb free package are available



### ■ ORDER INFORMATION

| Order codes  |           | Package | Packing        |
|--------------|-----------|---------|----------------|
| Halogen-free | Halogen   |         |                |
| N/A          | MBR30100E | TO-263  | 800pieces/Reel |

### ■ MAXIMUM RATINGS (Each diode leg)

| Parameter  | Symbol         | Value        | Unit |
|--|----------------|--------------|------|
| Peak repetitive reverse voltage  | $V_{RRM}$      | 100          | V    |
| Average rectified output current   | Total          | 30           | A    |
|  | Per leg        | 15           | A    |
| Non-repetitive peak forward surge current 8.3ms single half sine-wave superimposed on reate load | $I_{FSM}$      | 250          | A    |
| Operating and storage temperature range  | $T_J, T_{STG}$ | -55 to + 175 | °C   |

### ■ ELECTRICAL CHARACTERISTICS( $T_A=25^\circ\text{C}$ Unless otherwise specified)

| Parameter                              | Symbol           | Conditions                               | Min | Typ  | Max  | Unit |
|--|------------------|--|-----|------|------|------|
| Peak repetitive reverse voltage        | $B_V$            | $I_C=0.5\text{mA}, T_J=25^\circ\text{C}$ | 100 | -    | -    | V    |
| Forward voltage drop                   | $V_F$            | $I_F=15\text{A}, T_J=25^\circ\text{C}$   | -   | 0.83 | 0.86 | V    |
| Typical junction capacitance per diode | $C_J$            | $V_R=4\text{V}, f=1\text{MHz}$           | -   | 395  | -    | pF   |
| Leakage current                        | $I_R$            | $V_R=100\text{V}, T_J=25^\circ\text{C}$  | -   | -    | 0.05 | mA   |
|  |                  | $V_R=100\text{V}, T_J=125^\circ\text{C}$ | -   | -    | 20   |      |
| Typical thermal resistance per diode   | $R_{\theta J-A}$ |  | -   | 50   | -    | °C/W |
|  | $R_{\theta J-C}$ |  | -   | 2    | -    |      |

■ TYPICAL CHARACTERISTICS

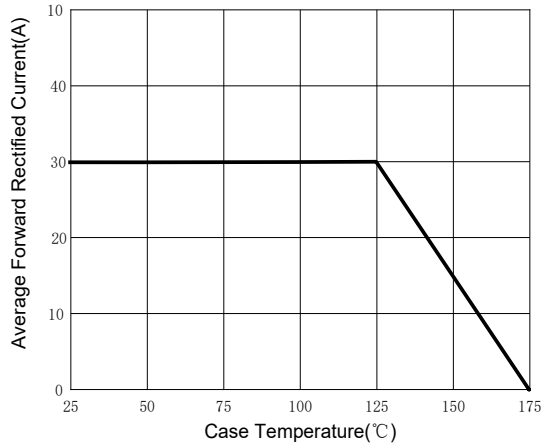


Fig.1: Forward Current Derating Curve

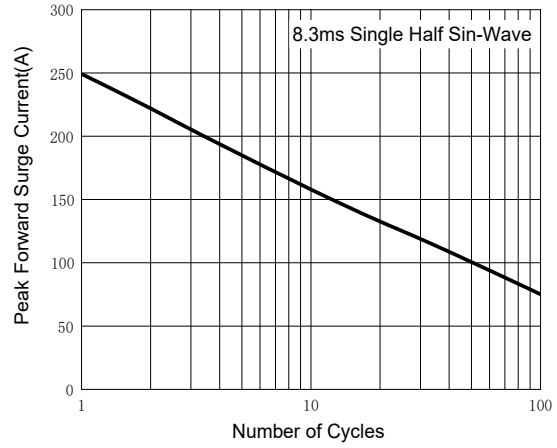


Fig.2: Forward Surge Current Capability (Per Diode)

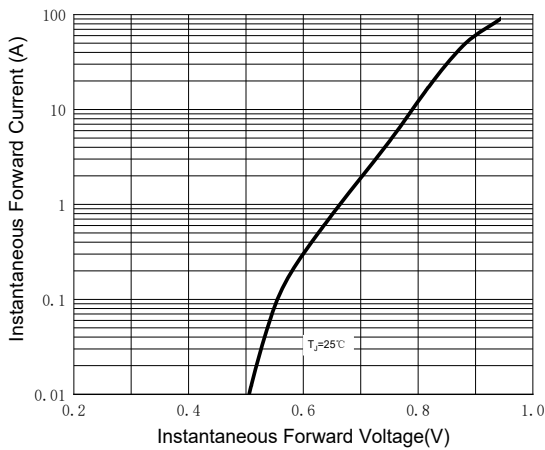


Fig.3: Typical Instantaneous Forward Characteristics (Per Diode)

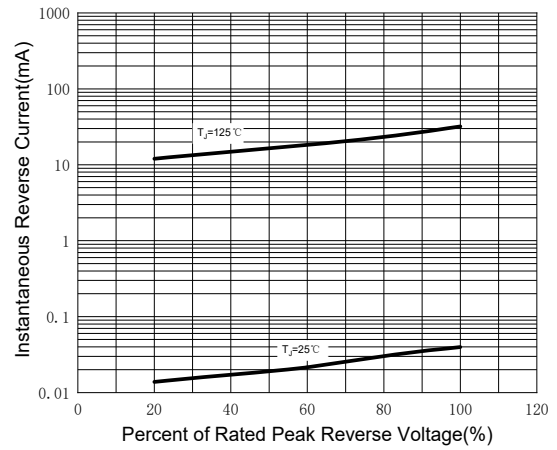


Fig.4: Typical Reverse Leakage Characteristics (Per Diode)

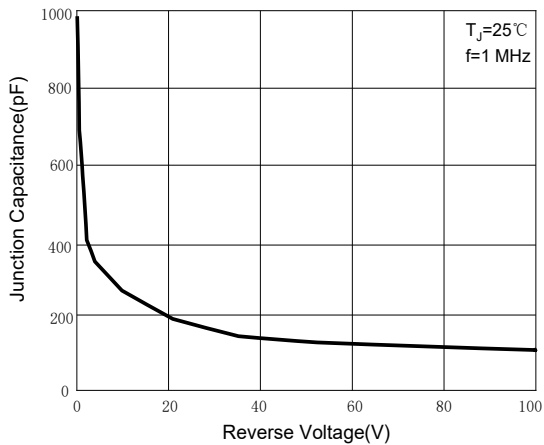


Fig.5: Typical Junction Capacitance (Per Diode)

**■ TO-263 PACKAGE OUTLINE DIMENSIONS**
